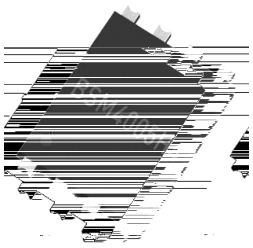
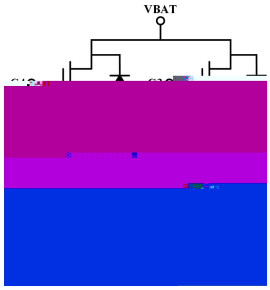
40 V	4mΩ @V_{GS} = 10V	50 A

- N -
- AEC-Q101 PPAP
- 175°C
- 100% Rg
- Wettable Flank AOI





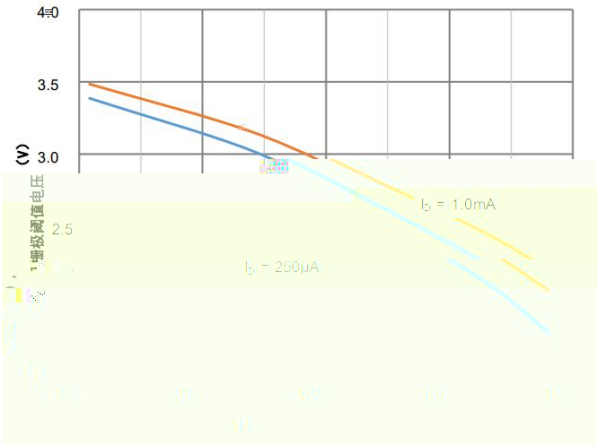




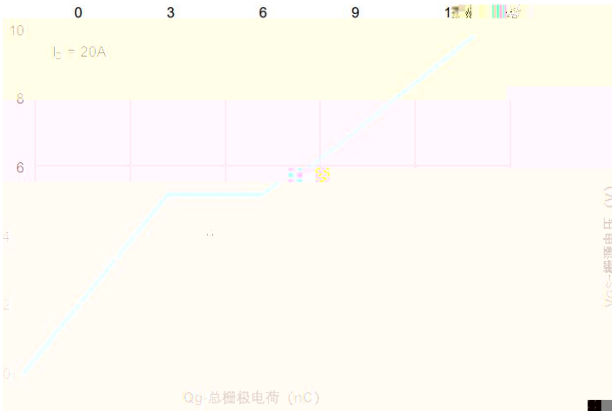
	V_{DS}	40	V
	V_{GS}		

	$V_{(BR)DSS}$	V_{GS} = 0V, I_D = 250μA	40			V
	I_{DSS}	V_{DS} = 40V, V_{GS} = 0V			1.0	μA
		T_J = 125°C			100	μA
	I_{GSS}	V_{GS} = ±20V, V_{DS} = 0V			±100	μA
	$V_{GS(th)}$	V_{GS} = V_{DS}, I_D = 250μA	2.0	3.0	4.0	V
-	$R_{DS(ON)}$	V_{GS} = 10V, I_D = 20A		4.0	4.7	mΩ
	g_{fs}	V_{DS} = 5.0V, I_D = 20A		15		S
	V_{SD}	I_S = 2.0A, V_{GS} = 0V		0.7	1.2	V
	C_{iss}	V_{DS} = 20V, V_{GS} = 0V, f = 1MHz		982		pF
	C_{oss}			593		pF
	C_{rss}			25		pF
	R_g	V_{GS} = 0V, V_{DS} = 0V, f = 1MHz		4.2		Ω
	$t_{d(on)}$	V_{GS} = 10V, V_{DS} = 20V, I_D = 20A, R_{GEN} = 3.0Ω		5.7		ns
	t_r			11		ns
	$t_{d(off)}$			14		ns
	t_f			8.0		ns
VGS=10V	Q_g	V_{DS} = 20V, I_D = 20A V_{GS} = 10V		14		nC
	Q_g			8.7		nC

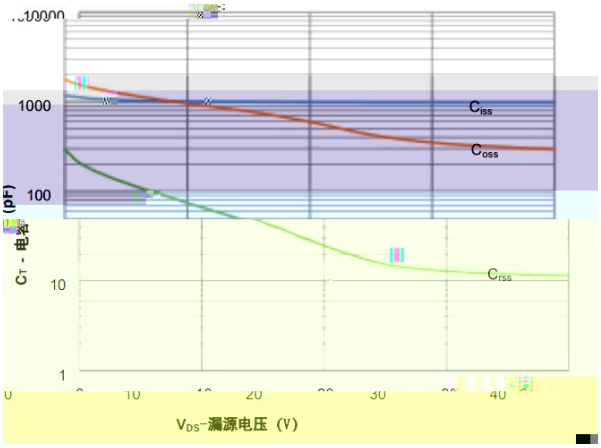
VGS=6.0V			
	Q_{gd}	2.9	nC
	Q_{gs}	4.6	nC


4.0
3.5
3.0
(V)
2.5
I_D = 1.0mA
I_D = 250μA

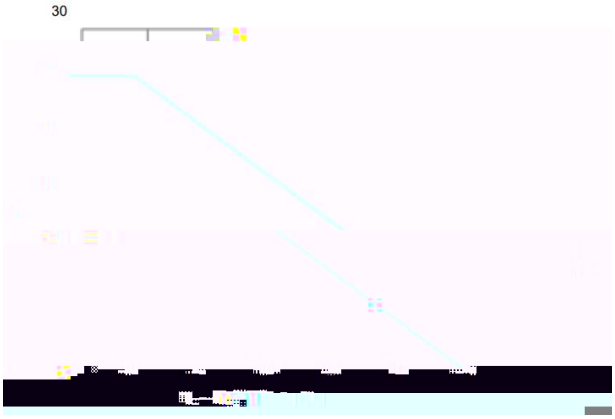
7


0
3
6
9
10
I_D = 20A
8
6
Qg-总栅极电荷（nC）

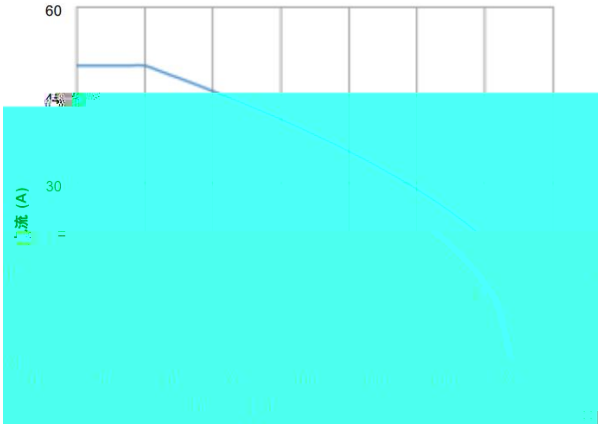
8


10000
1000
100
10
1
(pF)
C_{iss}
C_{oss}
C_{rss}
0
10
20
30
40
V_{DS}-漏源电压（V）

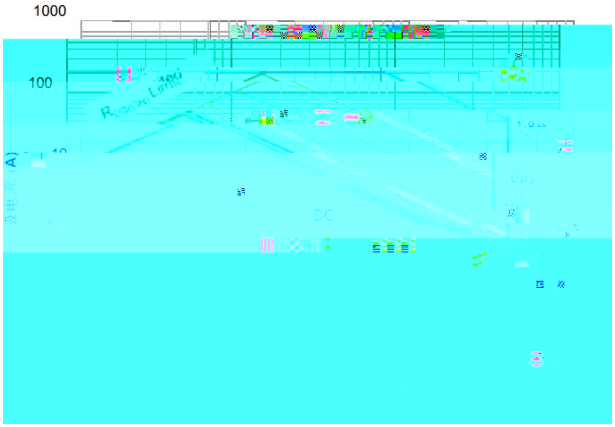
9


30

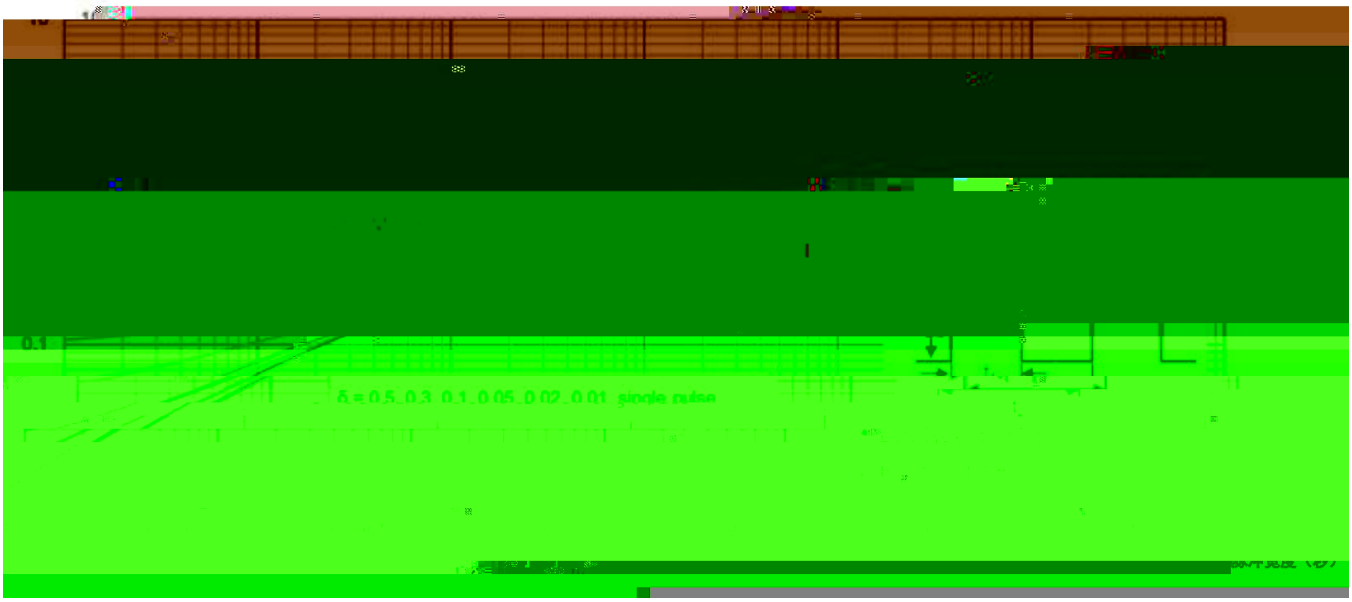
10


60
30
(A)

11

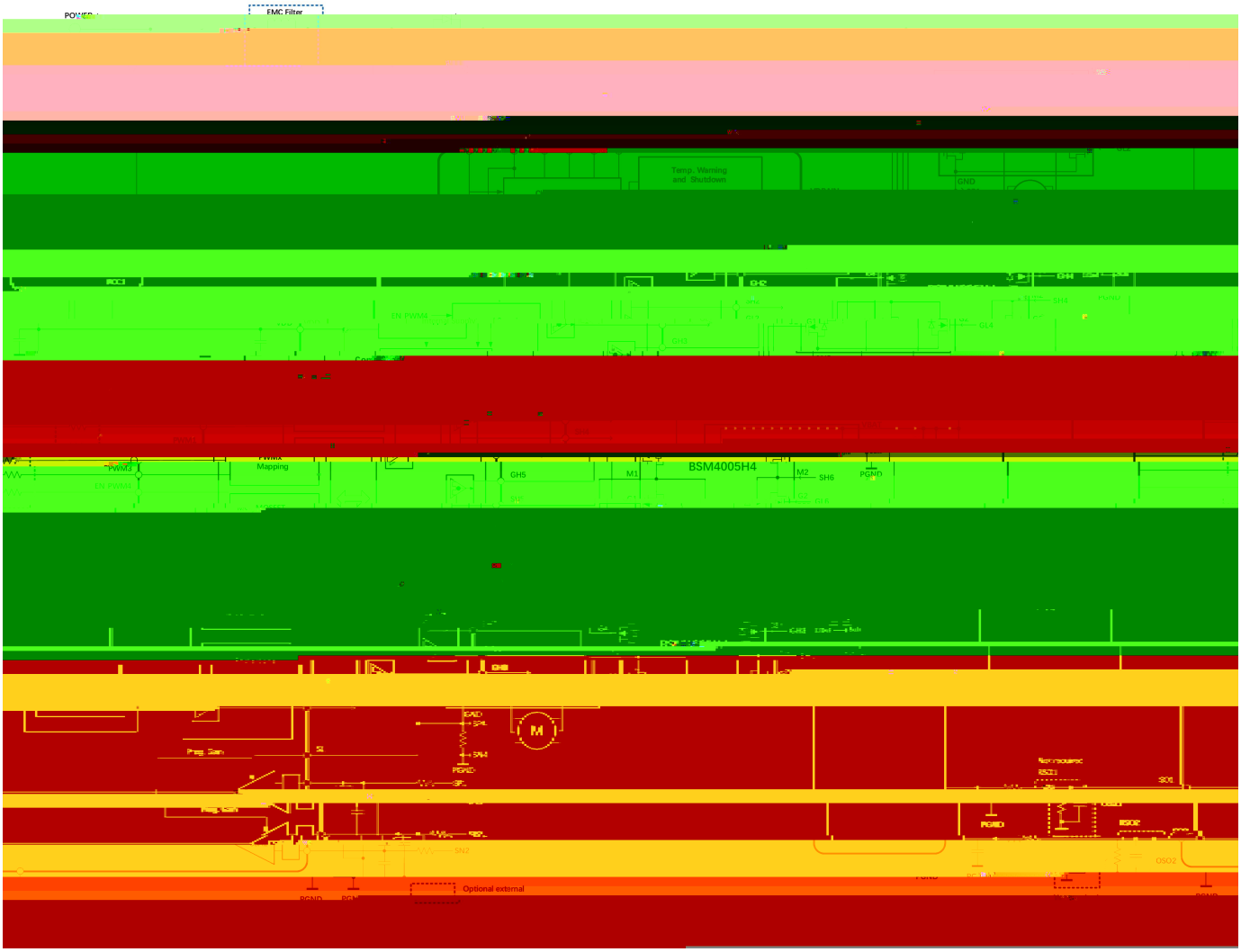

1000
100
A)
DC

12



13

/



14

Note

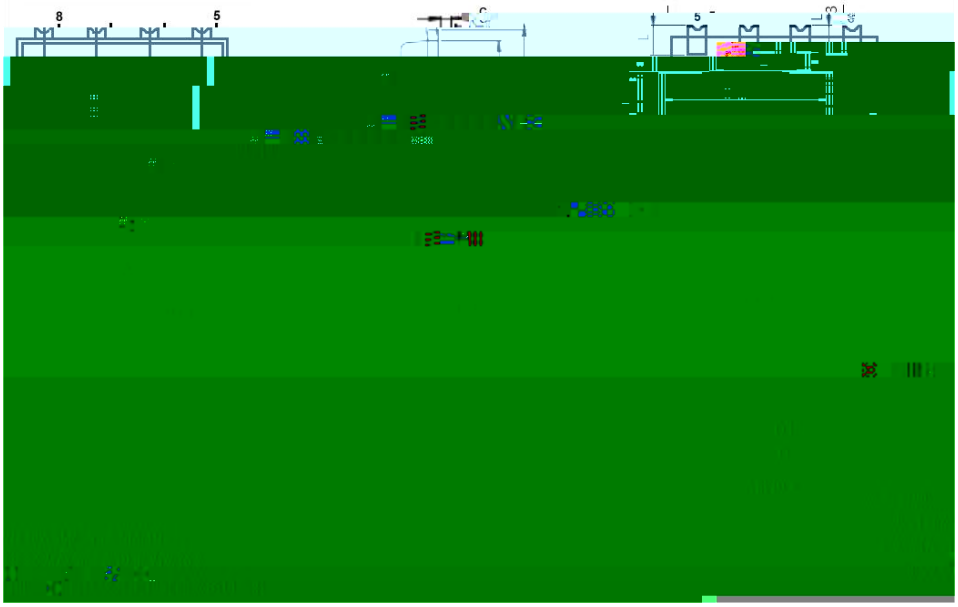
PGND

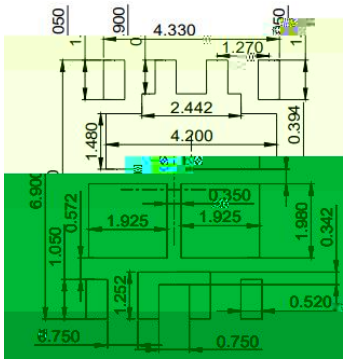
GND BSM4005H4 GND

SP3 SN3 SP4 SN3

/

封装外形





DIM.	MILLIMETER		
	MIN.	NOM.	MAX